

02/02/98  
1c572 U.S. PRO

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of )

ELIYAHOU HARARI, ROBERT D. )  
NORMAN and SANJAY MEHROTRA )

Serial No.: 08/771,708 )

Filed: December 20, 1996 )

For: FLASH EEprom SYSTEM )

Group Art Unit: 2785

#4 Prec  
J. Roberts  
Feb 13/1998

San Francisco, California

Assistant Commissioner for Patents  
Washington, D.C. 20231

By Express Mail #: EM215669675US  
Dated: February 2, 1998

THIRD PRELIMINARY AMENDMENT TRANSMITTAL

Sir:

Transmitted herewith is a Third Preliminary Amendment in  
the captioned application, of which no additional fee is required.

Respectfully submitted,

Dated: February 2, 1998

Gerald P. Parsons  
Gerald P. Parsons, Reg. No. 24,486  
MAJESTIC, PARSONS, SIEBERT & HSUE  
Four Embarcadero Center, Suite 1100  
San Francisco, CA 94111-4106  
Telephone: (415) 248-5500  
Facsimile: (415) 362-5418

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**THIRD PRELIMINARY AMENDMENT**

Sir:

Please further amend certain of the claims of the above-identified patent application, prior to a substantive examination thereof, as follows:

163. (Twice Amended) A method of operating an EEprom system having memory cells that individually include an electrically floating gate carrying a charge level that is alterable in response to appropriate voltage conditions being applied to the cell in order to set a variable threshold level thereof into a range that is determinable by reading the cell [to be in one of at least two defined threshold level regions], said method comprising:

applying said appropriate voltage conditions in parallel to a plurality of said memory cells [in parallel], thereby to alter the charge levels on the floating gates of said plurality of memory cells,

determining the threshold level [regions] ranges [of] in which individual ones of said plurality of memory cells lie, and

terminating said application of appropriate voltage conditions to individual ones of said plurality of memory cells